Power transistor (60V, 3A)

2SC5826

Features

1) High speed switching.

(tf: Typ.: 30ns at Ic = 3A)

2) Low saturation voltage, typically

(Typ.: 200mV at Ic = 2A, IB = 0.2mA)

3) Strong discharge power for inductive load and capacitance load.

4) Complements the 2SA2073

Applications

Low frequency amplifier High speed switching

Structure

NPN Silicon epitaxial planar transistor

Packaging specifications

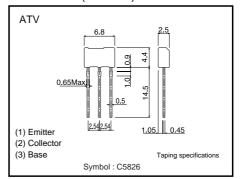
	Package	Taping
Туре	Code	TV2
	Basic ordering unit (pieces)	2500
2SC5826		0

● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vсво	60	V	
Collector-emitter voltage		Vceo	60	V	
Emitter-base voltage		VEBO	6	V	
Collector current	DC	Ic	3	А	
	Pulsed	Іср	6	Α *	
Power dissipation		Pc	1.0	W	
Junction temperature		tj	150	°C	
Range of storage temperature		tstg	-55 to 150	°C	

^{*}Pw=100ms

●Dimensions (Unit:mm)



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
Collector-emitter breakdown voltage	BVceo	60	-	_	V	Ic=1mA	
Collector-base breakdown voltage	ВУсво	60	_	_	V	Ic=100μA	
Emitter-base breakdown voltage	ВVево	6	_	_	V	Iε=100μA	
Collector cut-off current	Ісво	-	-	1.0	μΑ	Vcb=40V	
Emitter cut-off current	ІЕВО	-	-	1.0	μΑ	V _{EB} =4V	
Collector-emitter saturation voltage	VCE (sat)	-	- 200	500	mV	Ic=2A *1	
						Iв=0.2A	
DC current gain	hfe	FE 120		- 390	-	Vce=2V	
			_			Ic=100mA	
Transition frequency	fτ	fr –	- 200	-	MHz	Vc=10V *1	
						IE= -100mA	
						f=10MHz	
Corrector output capacitance	Cob	Cob –	20 -		– pF	Vcb=10V	
				20 –		IE=0mA	
						f=1MHz	
Turn-on time	ton	-	50	-	ns	Ic=3A *2	
Storage time	tstg	-	150	-	ns	Iв1=300mA Iв2= –300mA	
Fall time	tf	-	30	-	ns	Vcc≑25V	

●hFE RANK

Q	R
120–270	180-390

•Electrical characteristic curves

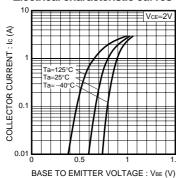


Fig.1 Grounded Emitter **Propagation Characteristics**

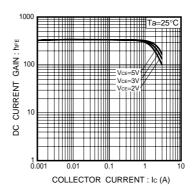


Fig.2 DC Current Gain vs.

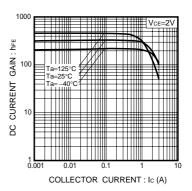


Fig.3 DC Current Gain vs. Collector Current (II)

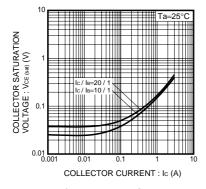


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (I)

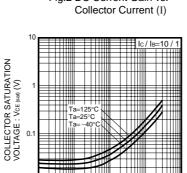


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (II)

COLLECTOR CURRENT : Ic (A)

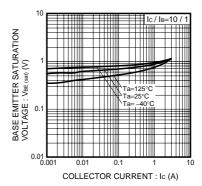


Fig.6 Base-Emitter Saturation Voltage vs. Collecter Current

^{*1} Non repetitive pulse *2 See Switching charactaristics measurement circuits

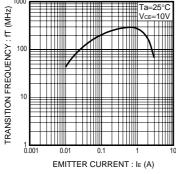


Fig.7 Transition Frequency

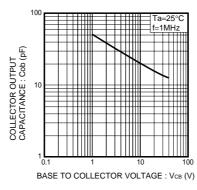


Fig.8 Collector Output Capacitance

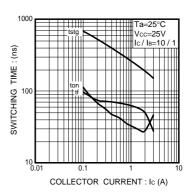


Fig.9 Switching Time

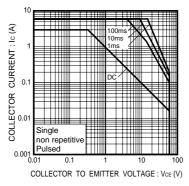
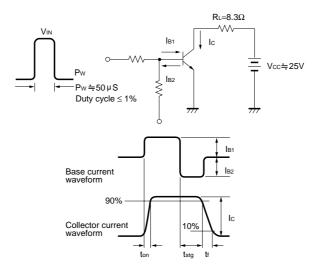


Fig.10 Safe Operating Area

•Switching characteristics measurement circuits



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